A B S T R A C T

SEMICONDUCTOR STRUCTURE ON AN EXTREMELY ROUGH SUBSTRATE

The invention relates to a semiconductor structure comprising:

- a substrate (10) or a base layer, having a surface with roughness of more than 0.5 nm rms or having chemistry that is incompatible with molecular bonding;
- a layer (14) of material selected from semiconductor materials;
- a layer (12) termed the bonding layer located between the substrate or base layer and the layer of material selected from semiconductor materials.

Translation of the title and the abstract as they were when originally filed by the Applicant. No account has been taken of any changes that may have been made subsequently by the PCT Authorities acting ex officio, e.g. under PCT Rules 37.2, 38.2, and/or 48.3.